



**N-Channel Enhancement-Mode Vertical DMOS FETs**

**Ordering Information**

BV <sub>DSS</sub> / BV <sub>DGS</sub>	R <sub>DS(ON)</sub> (max)	I <sub>D(ON)</sub> (min)	Order Number / Package		
			TO-92	TO-243AA*	Die**
600V	20Ω	0.25A	VN2460N3	VN2460N8	VN2460NW

\* Same as SOT-89 Product Supplied on 2000 piece carrier tape reels.

\*\* Die in wafer form.

**Features**

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C<sub>ISS</sub> and fast switching speeds
- Excellent thermal stability
- Integral Source-Drain diode
- High input impedance and high gain

**Applications**

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

**Absolute Maximum Ratings**

Drain-to-Source Voltage	BV <sub>DSS</sub>
Drain-to-Gate Voltage	BV <sub>DGS</sub>
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

\* Distance of 1.6 mm from case for 10 seconds.

**Product marking for TO-243AA:**

**VN4F\***

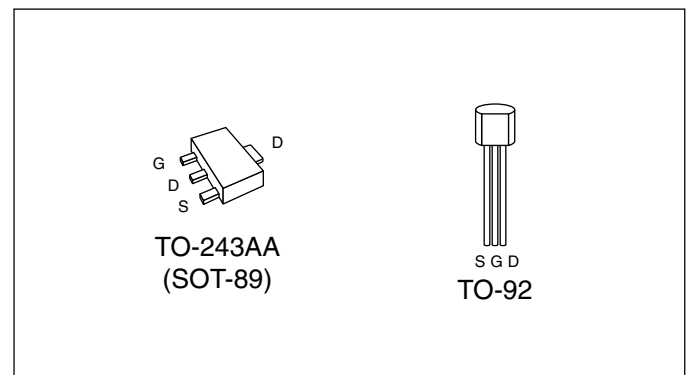
Where \* = 2-week alpha date code

**Advanced DMOS Technology**

These low threshold enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

**Package Options**



Note: See Package Outline section for dimensions.

## Thermal Characteristics

Package	$I_D$ (continuous)*	$I_D$ (pulsed)	Power Dissipation @ $T_C = 25^\circ\text{C}$	$\theta_{jc}$ $^\circ\text{C/W}$	$\theta_{ja}$ $^\circ\text{C/W}$	$I_{DR}^*$	$I_{DRM}$
TO-243AA	0.2A	0.6A	1.6W <sup>†</sup>	15	78 <sup>†</sup>	0.2A	0.6A
TO-92	0.16A	0.5A	1W	125	170	0.16A	0.5A

\*  $I_D$  (continuous) is limited by max rated  $T_j$ .

<sup>†</sup> Mounted on FR5 board, 25mm x 25mm x 1.57mm. Significant  $P_D$  increase possible on ceramic substrate.

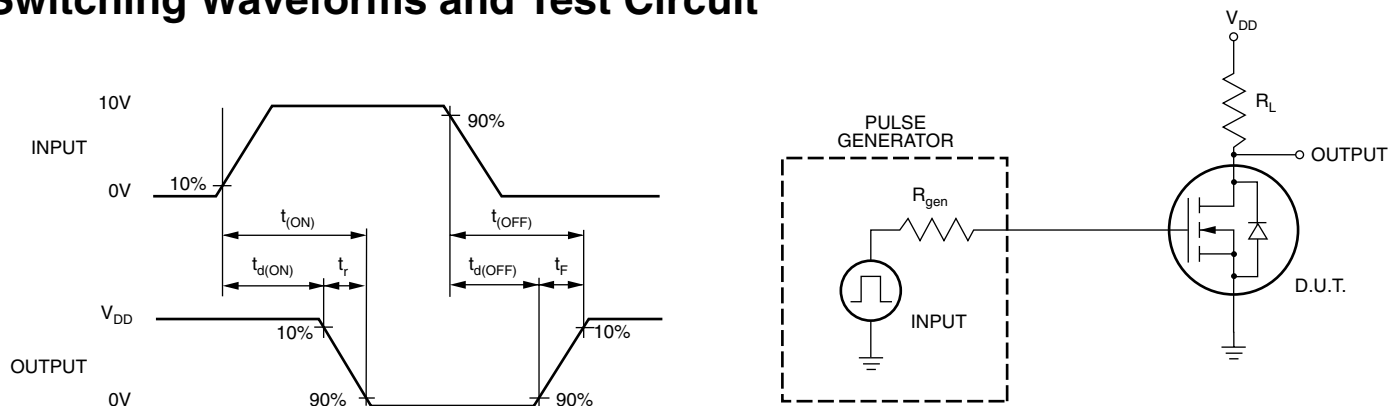
## Electrical Characteristics (@ $25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Unit	Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	600			V	$V_{GS} = 0V, I_D = 2.0mA$
$V_{GS(th)}$	Gate Threshold Voltage	1.5			V	$V_{GS} = V_{DS}, I_D = 2.0mA$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature			-5.5	mV/ $^\circ\text{C}$	$V_{GS} = V_{DS}, I_D = 2.0mA$
$I_{GSS}$	Gate Body Leakage			100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
$I_{DSS}$	Zero Gate Voltage Drain Current			10	$\mu\text{A}$	$V_{GS} = 0V, V_{DS} = \text{Max Rating}$
				1	mA	$V_{GS} = 0V, V_{DS} = 0.8 \text{ Max Rating}$ $T_A = 125^\circ\text{C}$
$I_{D(ON)}$	ON-State Drain Current	0.25			A	$V_{GS} = 10V, V_{DS} = 25V$
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance			25	$\Omega$	$V_{GS} = 4.5V, I_D = 100mA$
				20		$V_{GS} = 10V, I_D = 100mA$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature			1.7	%/ $^\circ\text{C}$	$V_{GS} = 10V, I_D = 100mA$
$G_{FS}$	Forward Transconductance	50			m $\bar{S}$	$V_{DS} = 25V, I_D = 100mA$
$C_{ISS}$	Input Capacitance			150	$\mu\text{F}$	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1.0 \text{ MHz}$
$C_{OSS}$	Common Source Output Capacitance			50		
$C_{RSS}$	Reverse Transfer Capacitance			25		
$t_{d(ON)}$	Turn-ON Delay Time			10	ns	$V_{DD} = 25V,$ $I_D = 250mA,$ $R_{GEN} = 25\Omega$
$t_r$	Rise Time			10		
$t_{d(OFF)}$	Turn-OFF Delay Time			25		
$t_f$	Fall Time			20		
$V_{SD}$	Diode Forward Voltage Drop			1.5	V	$V_{GS} = 0V, I_{SD} = 400mA$

### Notes:

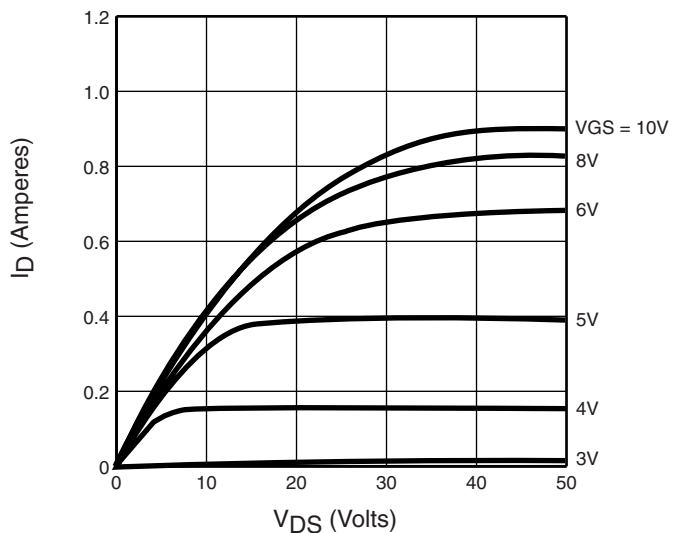
- All D.C. parameters 100% tested at  $25^\circ\text{C}$  unless otherwise stated. (Pulse test: 300 $\mu\text{s}$  pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

## Switching Waveforms and Test Circuit

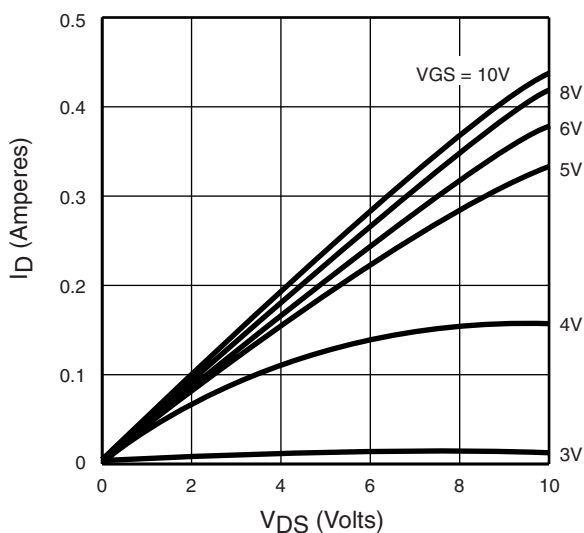


# Typical Performance Curves

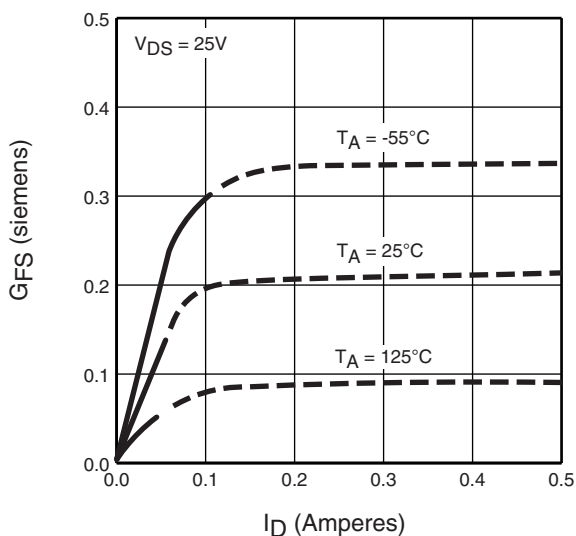
Output Characteristics



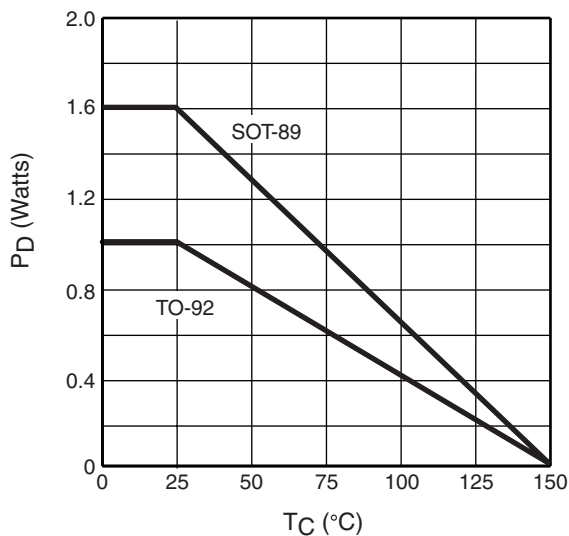
Saturation Characteristics



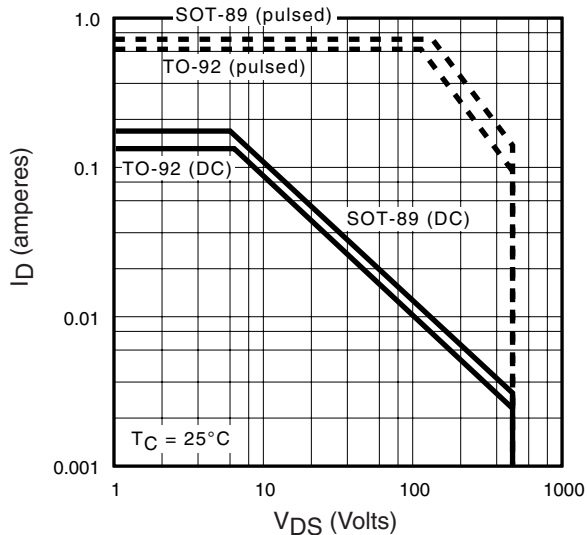
Transconductance vs. Drain Current



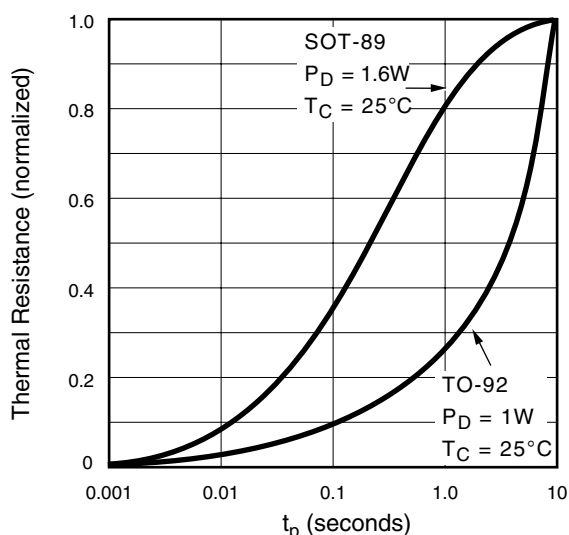
Power Dissipation vs. Case Temperature



Maximum Rated Safe Operating Area

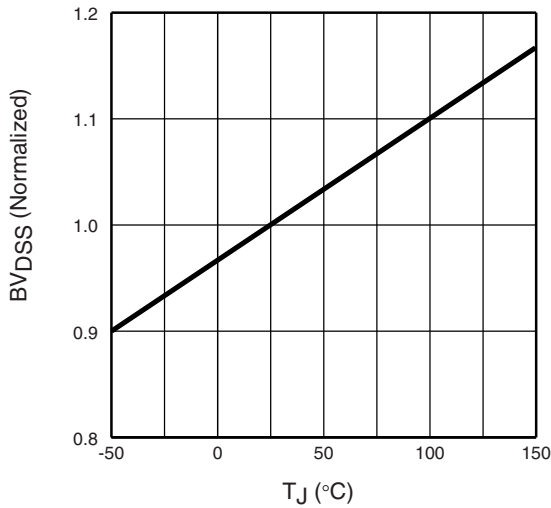


Thermal Response Characteristics

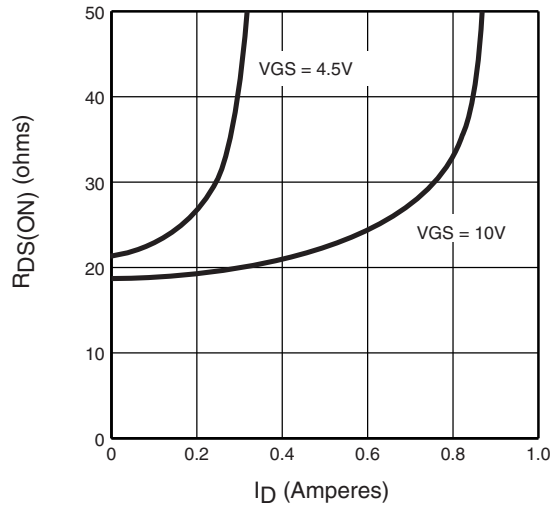


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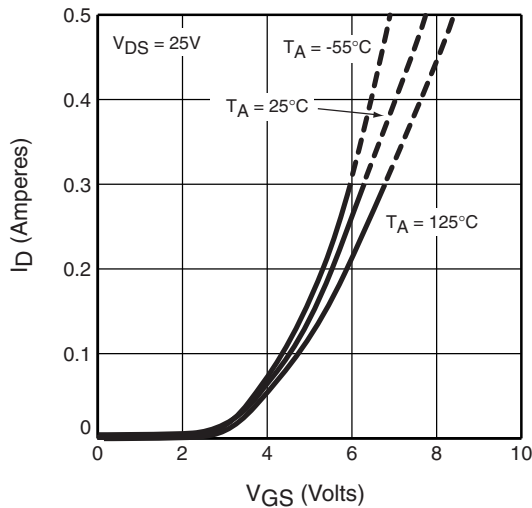
BV<sub>DSS</sub> Variation with Temperature



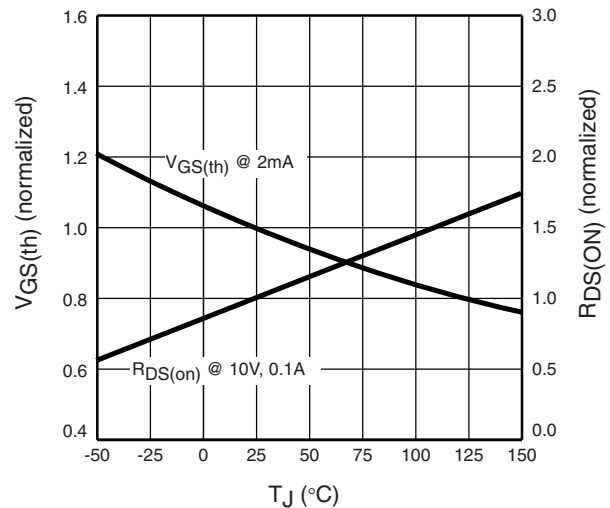
On Resistance vs. Drain Current



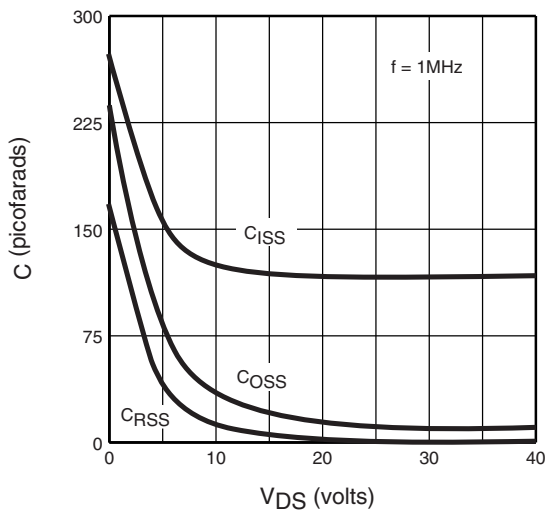
Transfer Characteristics



V<sub>GS(th)</sub> and R<sub>DS(ON)</sub> w/ Temperature



Capacitance vs. Drain Source Voltage



Gate Drive Dynamic Characteristics

